DATA SHEET

BYC8-600
Rectifier diode
Freewheeling and power factor correction

Product specification
File under Discrete Semiconductors, SC02

October 1997

Philips
Semiconductors

PHILIPS

Rectifier diode
Freewheeling and power factor correction

BYC8-600

GENERAL DESCRIPTION

Glass passivated, epitaxial rectifier diode in a plastic envelope. This diode has extremely fast reverse recovery time and low reverse recovery current and is designed specifically for use in forced commutation applications, for example:- as the output rectifier diode in power factor correction circuits operating in continuous conduction mode; or as a freewheeling diode in half-bridge and full-bridge switched mode power supplies.

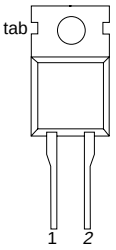
QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
$I_{F(AV)}$	Average forward current		8	A
V_{RRM}	Repetitive peak reverse voltage		600	V
V_F	Forward voltage		1.85	V
t_{rr}	Reverse recovery time	19		ns
I_{rrm}	Reverse recovery current		12	A

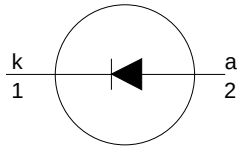
PINNING - TO220AC

PIN	DESCRIPTION
1	cathode (k)
2	anode (a)
tab	cathode (k)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	Repetitive peak reverse voltage		-	600	V
V_{RWM}	Crest working reverse voltage		-	600	V
V_R	Continuous reverse voltage	$T_{mb} \leq 110$ ˚C[1]	-	500	V
$I_{F(AV)}$	Average forward current	$\delta = 0.5$; with reapplied $V_{RRM(max)}$; $T_{mb} \leq 82$ ˚C[1]	-	8	A
$I_{F(RMS)}$	RMS forward current		-	11.3	A
I_{FRM}	Repetitive peak forward current	$\delta = 0.5$; with reapplied $V_{RRM(max)}$; $T_{mb} \leq 82$ ˚C[1]	-	16	A
I_{FSM}	Non-repetitive peak forward current.	t = 10 ms	-	55	A
		t = 8.3 ms	-	60	A
		sinusoidal; $T_j = 150$˚C prior to surge with reapplied $V_{RWM(max)}$			
I^2t	I^2t for fusing	t = 10 ms	-	15	A^2s
T_{stg}	Storage temperature		-40	150	˚C
T_j	Operating junction temperature		-	150	˚C

1 Maximum mounting base temperature limited by thermal runaway.

Rectifier diode
Freewheeling and power factor correction

BYC8-600

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	2.2	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air.	-	60	-	K/W

STATIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	I_F = 8 A; T_j = 150˚C	-	1.4	1.85	V
		I_F = 16 A; T_j = 150˚C	-	1.7	2.3	V
		I_F = 8 A;	-	2.0	2.8	V
I_R	Reverse current	V_R = 600 V	-	9	150	µA
		V_R = 500 V; T_j = 100 ˚C	-	1.1	3.0	mA

DYNAMIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{rr}	Reverse recovery time	I_F = 8 A to V_R = 400 V; dI_F/dt = 500 A/µs	-	19	-	ns
t_{rr}	Reverse recovery time	I_F = 8 A to V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 125˚C	-	32	40	ns
I_{rrm}	Peak reverse recovery current	I_F = 8 A to V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 125˚C	-	9.5	12	A
V_{fr}	Forward recovery voltage	I_F = 10 A; dI_F/dt = 100 A/µs	-	8	10	V

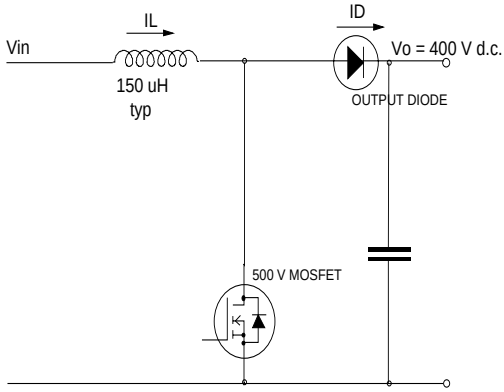


Fig.1. Typical application, output rectifier in boost converter power factor correction circuit. Continuous conduction, mode where the transistor turns on whilst forward current is still flowing in the diode.

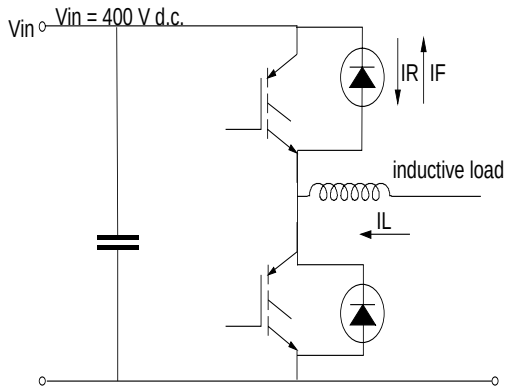


Fig.2. Typical application, freewheeling diode in half bridge converter. Continuous conduction mode, where each transistor turns on whilst forward current is still flowing in the other bridge leg diode.

Rectifier diode
Freewheeling and power factor correction

BYC8-600

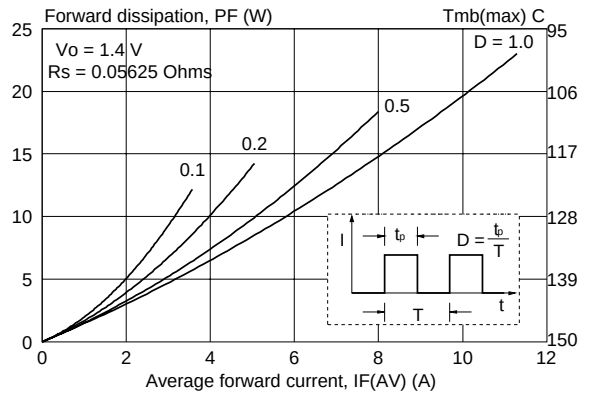


Fig.3. Maximum forward dissipation as a function of average forward current; rectangular current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

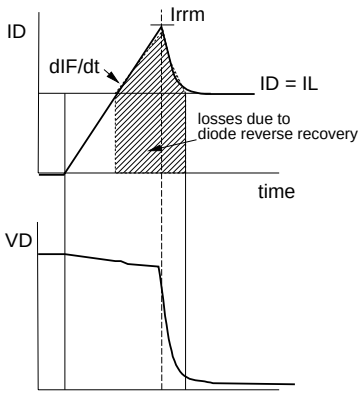


Fig.6. Origin of switching losses in transistor due to diode reverse recovery.

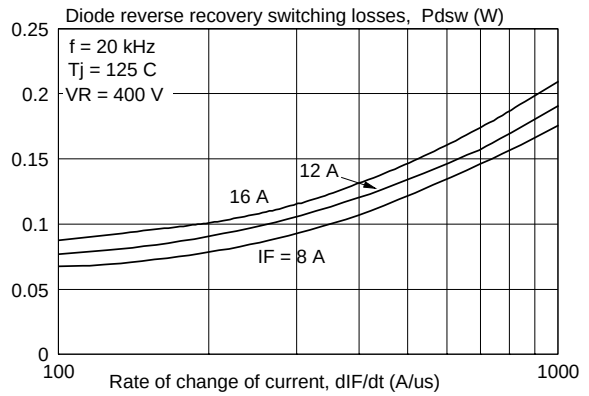


Fig.4. Typical reverse recovery switching losses in diode, as a function of rate of change of current dI_F/dt.

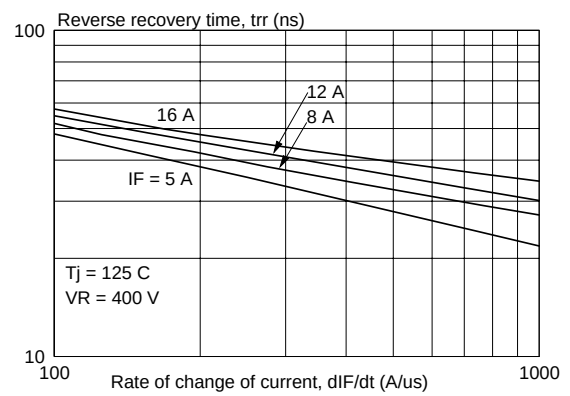


Fig.7. Typical reverse recovery time t_{rr}, as a function of rate of change of current dI_F/dt.

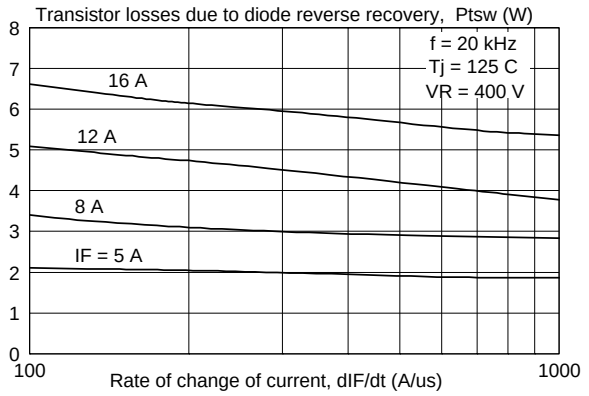


Fig.5. Typical switching losses in transistor due to reverse recovery of diode, as a function of of change of current dI_F/dt.

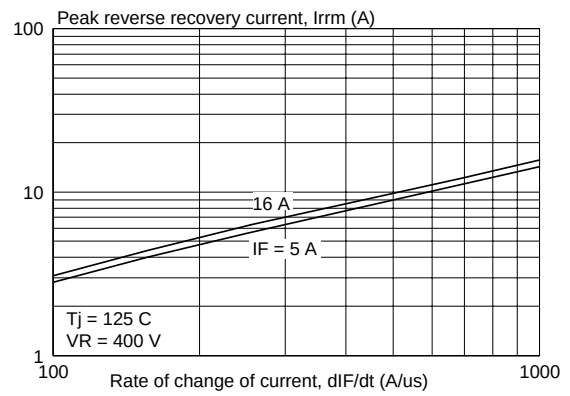


Fig.8. Typical peak reverse recovery current, I_{rrm} as a function of rate of change of current dI_F/dt.

Rectifier diode
Freewheeling and power factor correction

BYC8-600

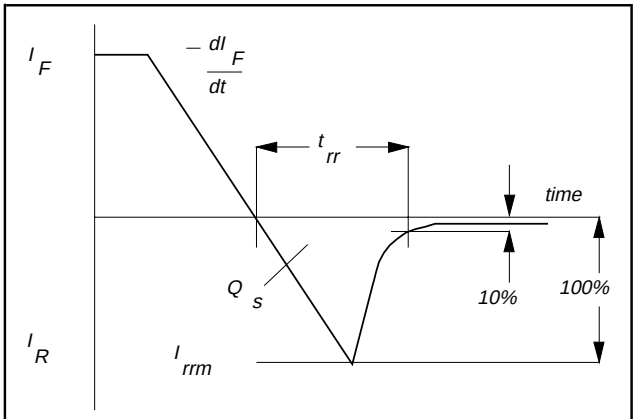


Fig.9. Definition of reverse recovery parameters t_{rr}, I_{rrm}

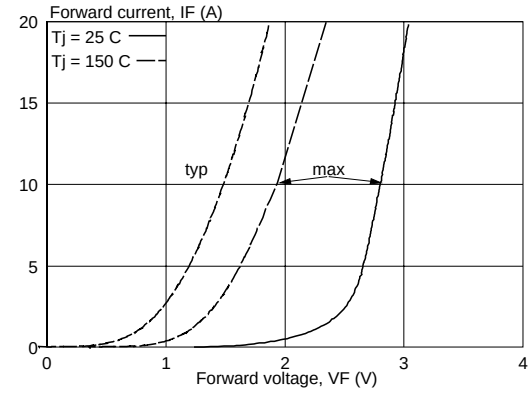


Fig.12. Typical and maximum forward characteristic $I_F = f(V_F)$; T_j = 25˚C and 150˚C.

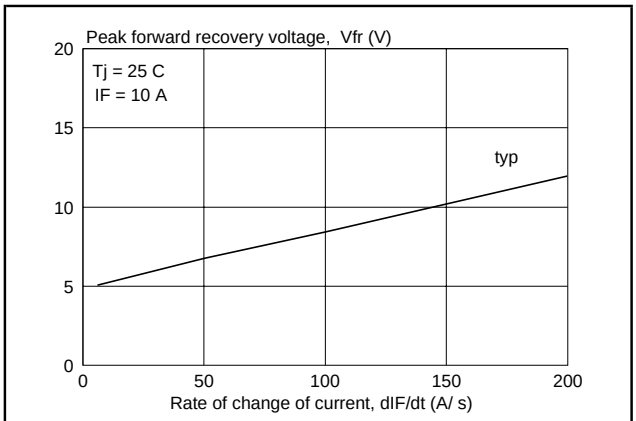


Fig.10. Typical forward recovery voltage, V_{fr} as a function of rate of change of current dI_F/dt.

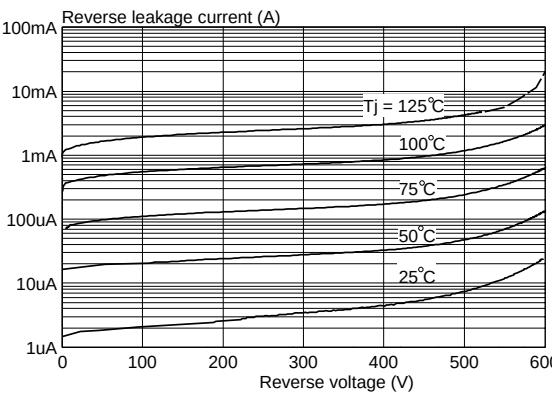


Fig.13. Typical reverse leakage current as a function of reverse voltage. $I_R = f(V_R)$; parameter T_j

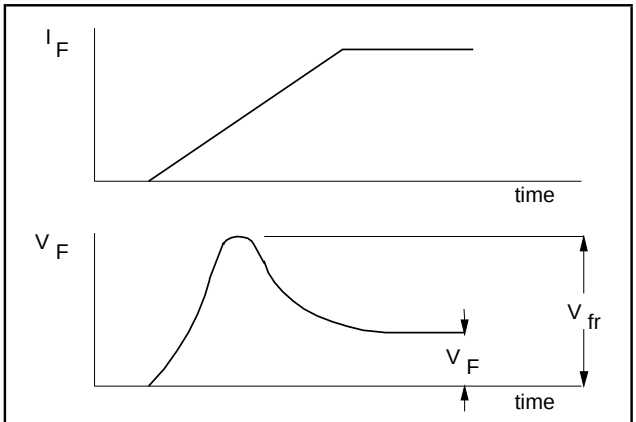


Fig.11. Definition of forward recovery voltage V_{fr}

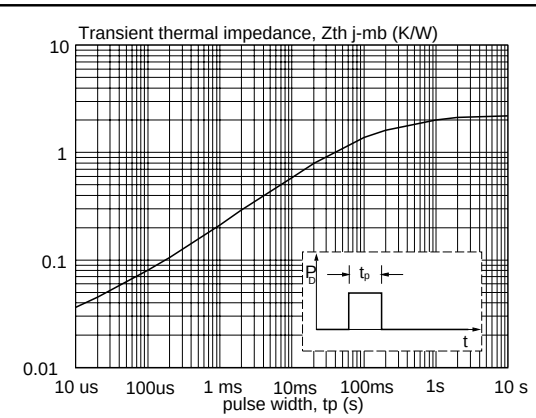


Fig.14. Maximum thermal impedance $Z_{th\ j\text{-}mb}$ as a function of pulse width.

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

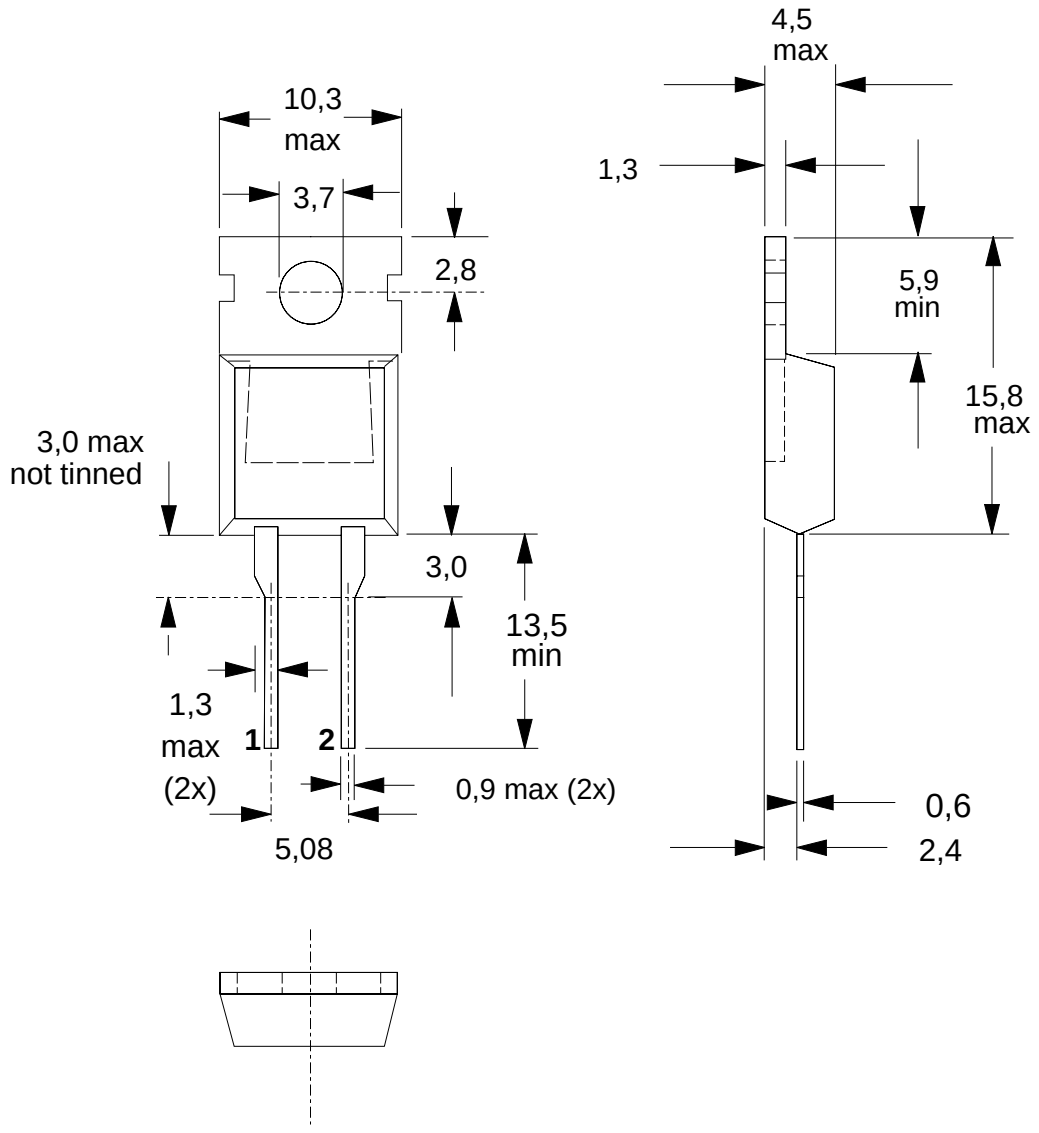


Fig.15. TO220AC; pin 1 connected to mounting base.

Notes
1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010,
Fax. +43 160 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 0044

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 SÃO PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 3 301 6312, Fax. +34 3 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 632 2000, Fax. +46 8 632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2686, Fax. +41 1 481 7730

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 625 344, Fax.+381 11 635 777

For all other countries apply to: Philips Semiconductors,
International Marketing & Sales Communications, Building BE-p,
P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

Internet: http://www.semiconductors.philips.com

SCA56

Printed in The Netherlands 137027/600/01/pp7 Date of release: October 1997 Document order number: 9397 750 03033

Let's make things better.

Philips Semiconductors

PHILIPS